



IDT-1651

JAN 1/22

SN: 09/838,084

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Guo-Qiang Lo, et al.

Assignee: Integrated Device Technology, Inc.

Title: DIELECTRIC ANTI-REFLECTIVE COATING SURFACE
TREATMENT TO PREVENT DEFECT GENERATION IN
ASSOCIATED WET CLEAN

Serial No: 09/838,084 Group No.: 2823

Filed: 4/18/2001 Examiner: Suk-San Foong

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January 22, 2003

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ASSISTANT COMMISSIONER FOR PATENTS
Washington, D. C. 20231

RESPONSE TO FIRST OFFICE ACTION

Sir:

Applicants submit the following remarks and amendments
in response to the Office Action dated October 22, 2002.

IN THE CLAIMS

Rewrite Claims 1 and 13 as follows.

1. (Amended) A method for preventing the formation of
watermark defects in a semiconductor process, the method
comprising:

a' patterning a silicon oxynitride layer; then
 etching a trench in a semiconductor substrate
 through the patterned silicon oxynitride layer; then
 conditioning the patterned silicon oxynitride
 layer, wherein no wet clean step is performed between
 the etching of the trench and the conditioning of the
 patterned silicon oxynitride layer; and then